

2N5460, 2N5461, 2N5462

JFET Amplifier P-Channel – Depletion

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

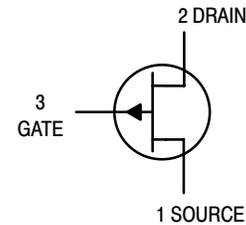
Rating	Symbol	Value	Unit
Drain – Gate Voltage	V_{DG}	40	Vdc
Reverse Gate – Source Voltage	V_{GSR}	40	Vdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Junction Temperature Range	T_J	-65 to +135	$^\circ\text{C}$
Storage Channel Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



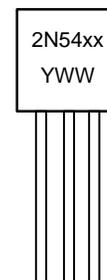
ON Semiconductor®

<http://onsemi.com>



TO-92
CASE 29
STYLE 7

MARKING DIAGRAM



Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Gate-Source Breakdown Voltage (I _G = 10 μAdc, V _{DS} = 0)	2N5460, 2N5461, 2N5462	V _{(BR)GSS}	40	-	-	Vdc
Gate Reverse Current (V _{GS} = 20 Vdc, V _{DS} = 0)	2N5460, 2N5461, 2N5462	I _{GSS}	-	-	5.0	nAdc
(V _{GS} = 30 Vdc, V _{DS} = 0)	2N5460, 2N5461, 2N5462	I _{GSS}	-	-	1.0	μAdc
(V _{GS} = 20 Vdc, V _{DS} = 0, T _A = 100°C)	2N5460, 2N5461, 2N5462	I _{GSS}	-	-	1.0	μAdc
(V _{GS} = 30 Vdc, V _{DS} = 0, T _A = 100°C)	2N5460, 2N5461, 2N5462	I _{GSS}	-	-	1.0	μAdc
Gate-Source Cutoff Voltage (V _{DS} = 15 Vdc, I _D = 1.0 μAdc)	2N5460 2N5461 2N5462	V _{GS(off)}	0.75 1.0 1.8	- - -	6.0 7.5 9.0	Vdc
Gate-Source Voltage (V _{DS} = 15 Vdc, I _D = 0.1 mAdc)	2N5460	V _{GS}	0.5	-	4.0	Vdc
(V _{DS} = 15 Vdc, I _D = 0.2 mAdc)	2N5461	V _{GS}	0.8	-	4.5	Vdc
(V _{DS} = 15 Vdc, I _D = 0.4 mAdc)	2N5462	V _{GS}	1.5	-	6.0	Vdc

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	2N5460 2N5461 2N5462	I _{DSS}	-1.0 -2.0 -4.0	- - -	-5.0 -9.0 -16	mAdc
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SMALL-SIGNAL CHARACTERISTICS

Forward Transfer Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	2N5460 2N5461 2N5462	y _{fs}	1000 1500 2000	- - -	4000 5000 6000	μmhos
Output Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)		y _{os}	-	-	75	μmhos
Input Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 MHz)		C _{iss}	-	5.0	7.0	pF
Reverse Transfer Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 MHz)		C _{rss}	-	1.0	2.0	pF

FUNCTIONAL CHARACTERISTICS

Equivalent Short-Circuit Input Noise Voltage (V _{DS} = 15 Vdc, V _{GS} = 0, f = 100 Hz, BW = 1.0 Hz)	e _n	-	60	115	nV/√Hz
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ORDERING INFORMATION

Device	Package	Shipping [†]
2N5460	TO-92	1000 Unit / Bulk
2N5460G	TO-92 (Pb-Free)	1000 Unit / Bulk
2N5461	TO-92	1000 Unit / Bulk
2N5461RLRA	TO-92	2000 Tape & Reel
2N5462	TO-92	1000 Unit / Bulk

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DRAIN CURRENT versus GATE SOURCE VOLTAGE

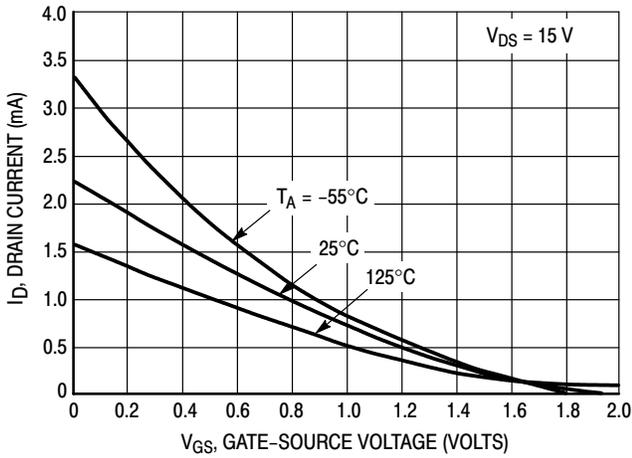


Figure 1. $V_{GS(off)} = 2.0$ V

FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

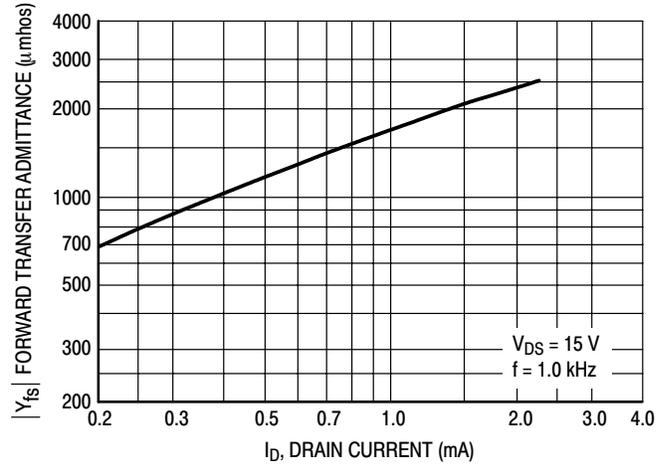


Figure 4. $V_{GS(off)} = 2.0$ V

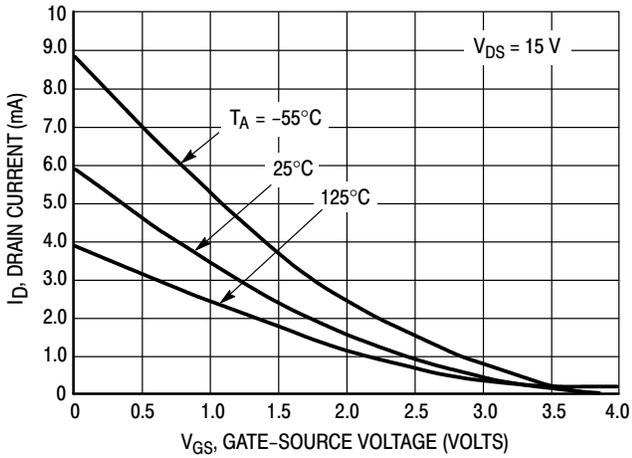


Figure 2. $V_{GS(off)} = 4.0$ V

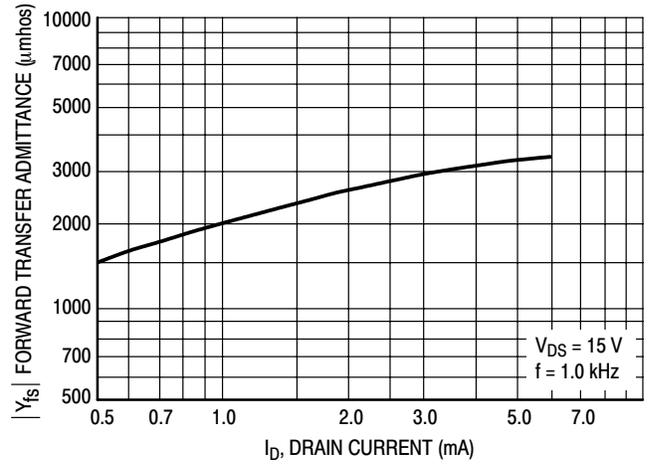


Figure 5. $V_{GS(off)} = 4.0$ V

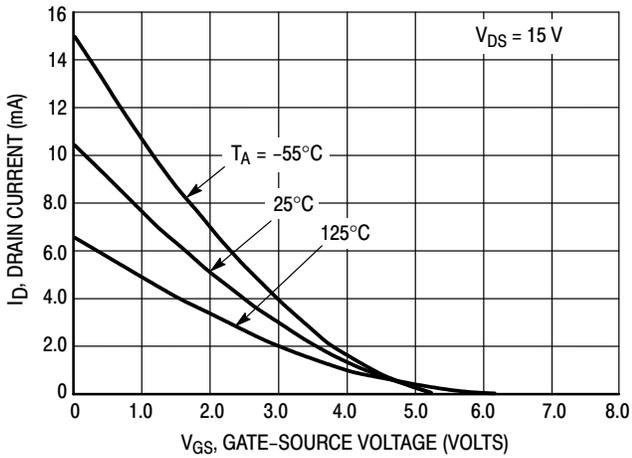


Figure 3. $V_{GS(off)} = 5.0$ V

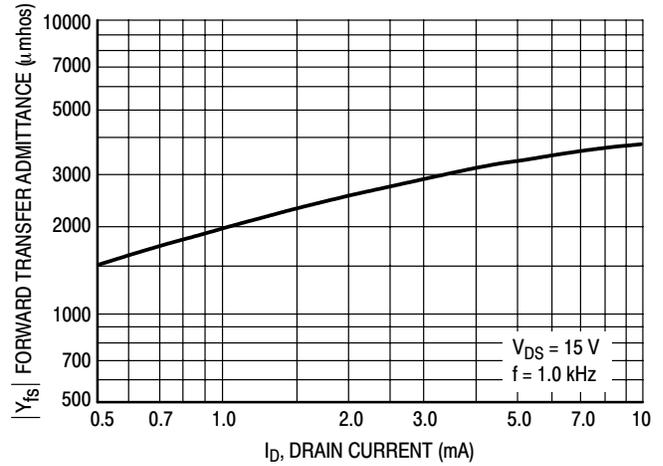


Figure 6. $V_{GS(off)} = 5.0$ V

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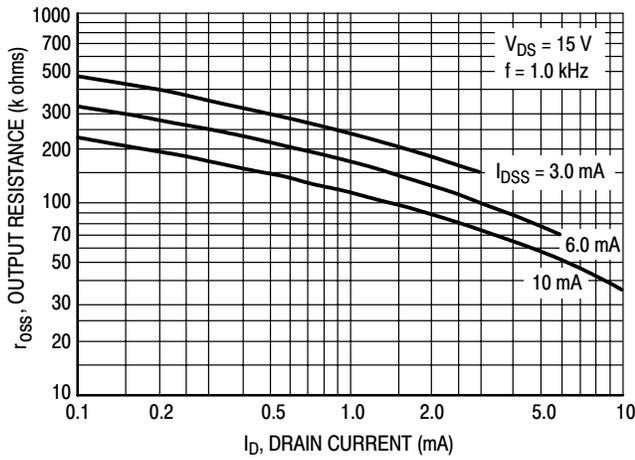


Figure 7. Output Resistance versus Drain Current

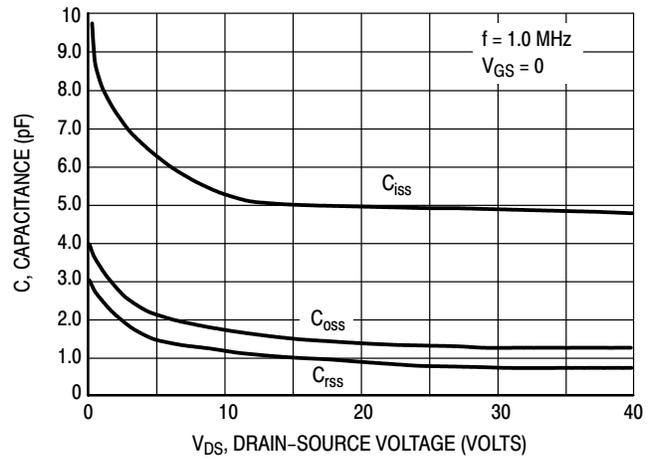


Figure 8. Capacitance versus Drain-Source Voltage

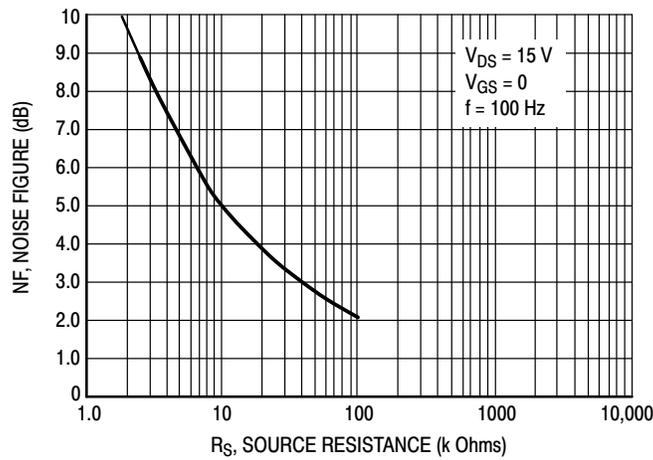
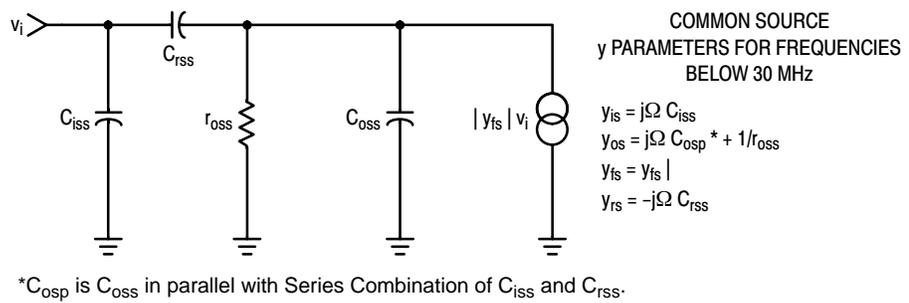


Figure 9. Noise Figure versus Source Resistance



NOTE:

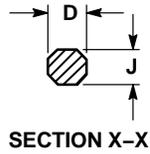
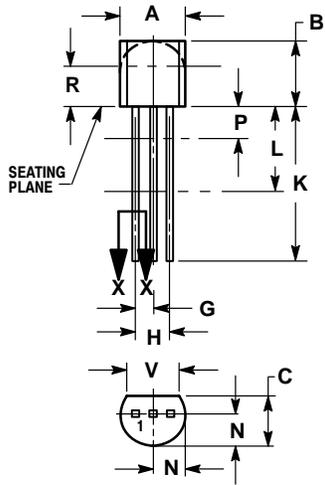
- Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

Figure 10. Equivalent Low Frequency Circuit

2N5460, 2N5461, 2N5462

PACKAGE DIMENSIONS

TO-92
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 7:

- PIN 1. SOURCE
2. DRAIN
3. GATE

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